



SANYO Semiconductors

DATA SHEET

PNP/NPN Epitaxial Planar Silicon Transistors

2SA1591/2SC4133

Switching Applications
(with Bias Resistance)

Applications

- Switching circuit, inverter circuit, interface circuit, driver circuit

Features

- On-chip bias resistance ($R_1=4.7k\Omega, R_2=47k\Omega$)
- Small-sized package (SPA)

(): 2SA1591

Absolute Maximum Ratings at $T_a=25^\circ C$

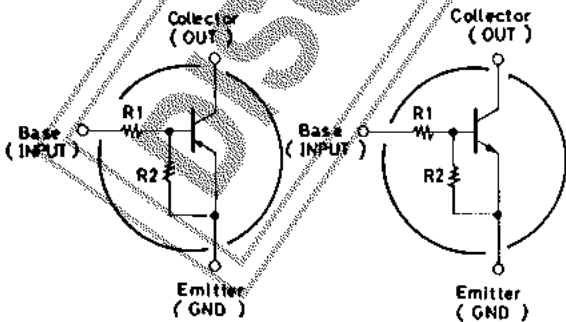
			unit
Collector to Base Voltage	V_{CB0}	(-)50	V
Collector to Emitter Voltage	V_{CE0}	(-)50	V
Emitter to Base Voltage	V_{EB0}	(-)6	V
Collector Current	I_C	(-)100	mA
Collector Current (Pulse)	I_{CP}	(-)200	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)0.1	μA
Collector Cutoff Current	I_{CEO}	$V_{CE}=(-)40V, I_B=0$			(-)0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$	(-)74	(-)97	(-)138	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)5V, I_C=(-)5mA$	70			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)5mA$		250		MHz
				(200)		
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		3.7		pF
				(5.5)		
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)10mA, I_B=(-)0.5mA$	(-)0.1	(-)0.3		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$	(-)50			V

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Electrical Connection

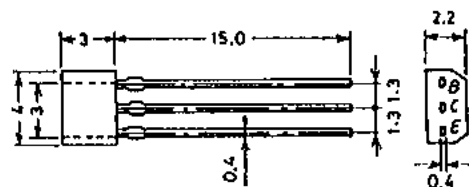


2SA1591 (PNP)

2SC4133 (NPN)

Case Outline 2033

(unit:mm)



B: Base
C: Collector
E: Emitter
SANYO: SPA

Specifications and information herein are subject to change without notice.

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		min	typ	max	unit	
Input OFF-State Voltage	$V_{I(off)}$	$V_{CE}=(-)5V, I_C=(-)100\mu A$	(-)0.5	(-)0.6	(-)0.8	V
Input ON-State Voltage	$V_{I(on)}$	$V_{CE}=(-)0.2V, I_C(-)5mA$	(-)0.7	(-)0.85	(-)1.3	V
Input Resistance	R_1		3.3	4.7	6.1	k Ω
Resistance Ratio	R_1/R_2		0.09	0.1	0.11	

